

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^{a, e}	Q _g (Typ.)
60	0.96 at V _{GS} = 10 V	220	70 nC
	1.55 at V _{GS} = 4.5 V	160	

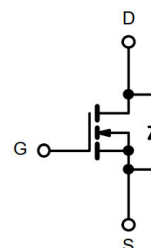
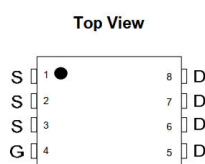
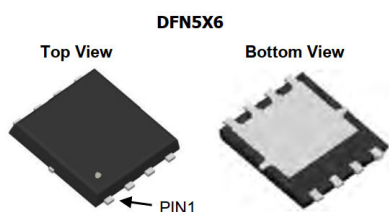
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified for Automotive Applications



APPLICATIONS

- Notebook PC Core
- VRM/POL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C)	I _D	220 ^{a, e}	A
		155 ^e	
		38 ^{b, c}	
		27 ^{b, c}	
Pulsed Drain Current	I _{DM}	800	mJ
Avalanche Current Pulse ^e	I _{AS}	86	
Single Pulse Avalanche Energy	E _{AS}	798	mJ
Continuous Source-Drain Diode Current	I _S	220 ^{a, e}	
		18 ^{b, c}	
Maximum Power Dissipation	P _D	298 ^a	W
		208	
		4.7 ^{b, c}	
		3.29 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	10	13	°C/W
Maximum Junction-to-Case	R _{thJC}	0.5	1	

Notes:

a. Based on T_C = 25 °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Calculated based on maximum junction temperature.

e. Single pulse width limited by junction temperature T_J(MAX)=150°C.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		15		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			-6.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 48 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	220			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 50 A		0.96	1.2	mΩ
		V _{GS} = 4.5 V, I _D =30 A		1.55	1.9	
Forward Transconductance ^a	g _{fs}	V _{DS} = 5 V, I _D =20 A		88		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		8900		pF
Output Capacitance	C _{oss}			5100		
Reverse Transfer Capacitance	C _{rss}			115		
Total Gate Charge	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 50 A		70		nC
Gate-Source Charge	Q _{gs}			28		
Gate-Drain Charge	Q _{gd}			13		
Gate Resistance	R _g	f = 1 MHz		2		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 48 V, R _L = 2.5 Ω I _D ≅ 50A, V _{GEN} = 10 V, R _g = 2 Ω		14		ns
Rise Time	t _r			60		
Turn-Off Delay Time	t _{d(off)}			56		
Fall Time	t _f			40		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			200	A
Pulse Diode Forward Current ^a	I _{SM}				800	
Body Diode Voltage	V _{SD}	I _S = 50 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs, T _J = 25 °C		68		ns
Body Diode Reverse Recovery Charge	Q _{rr}			259		nC
Reverse Recovery Fall Time	t _a			47		ns
Reverse Recovery Rise Time	t _b			55		

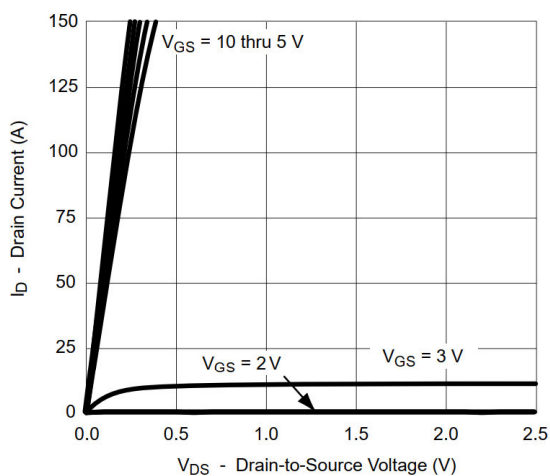
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

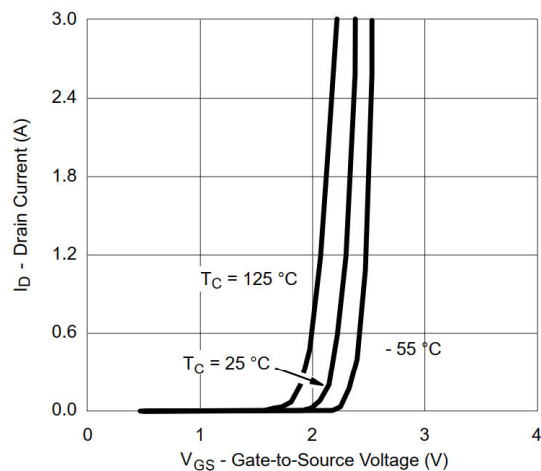
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

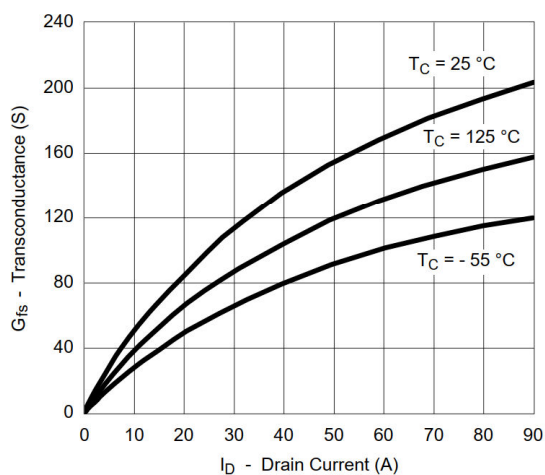
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



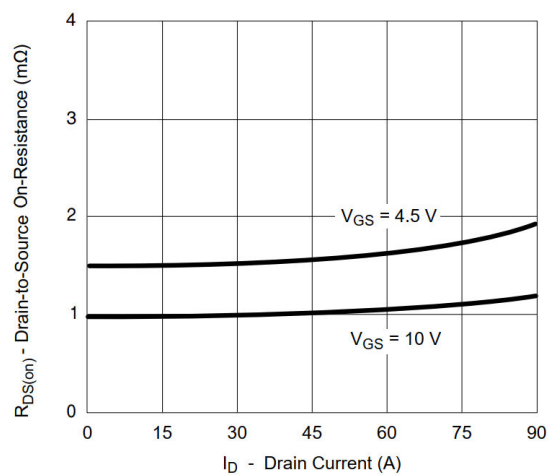
Output Characteristics



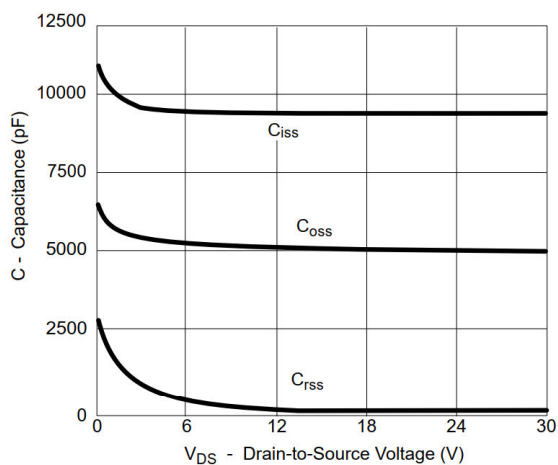
Transfer Characteristics



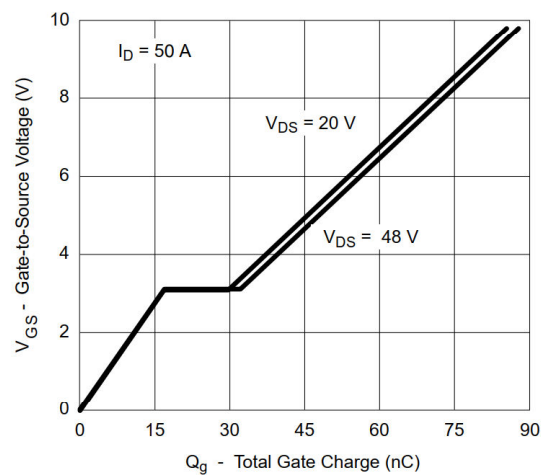
Transconductance



$R_{DS(on)}$ vs. Drain Current

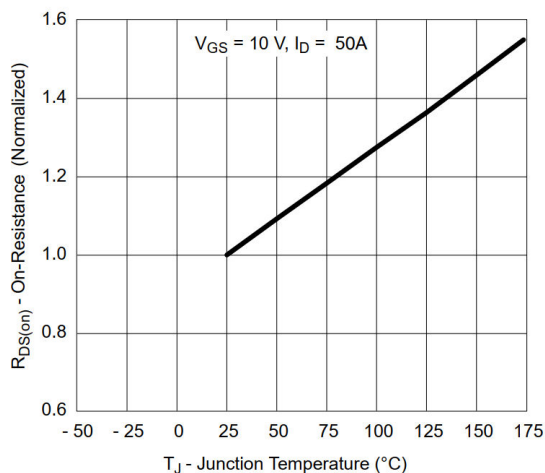


Capacitance

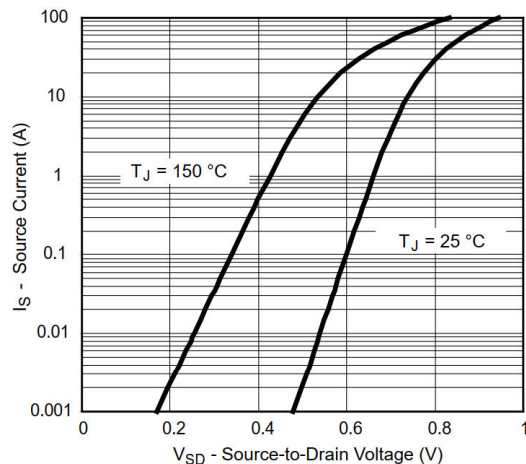


Gate Charge

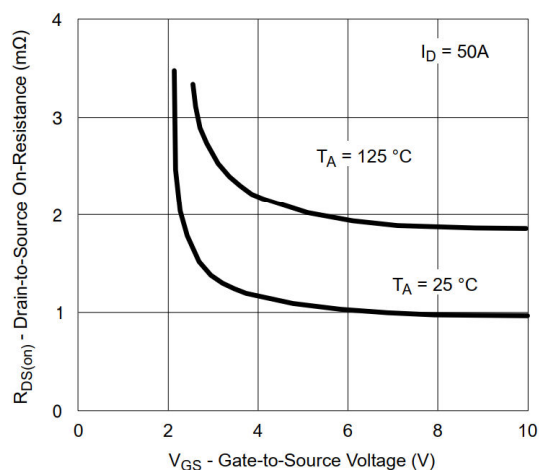
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



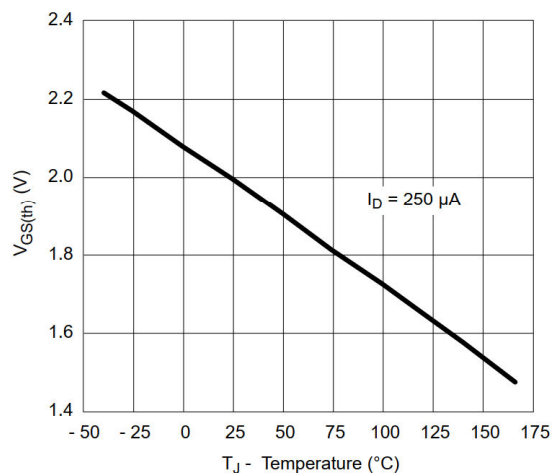
On-Resistance vs. Junction Temperature



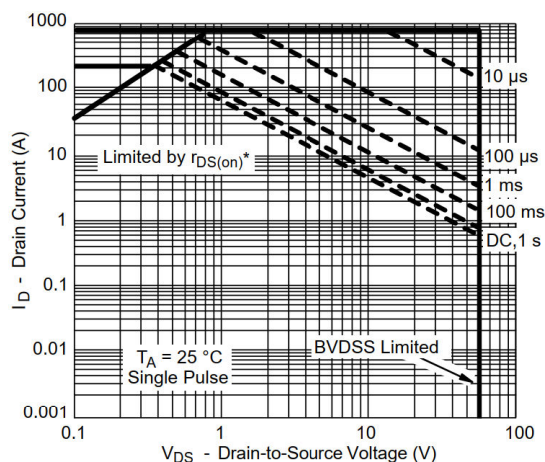
Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature

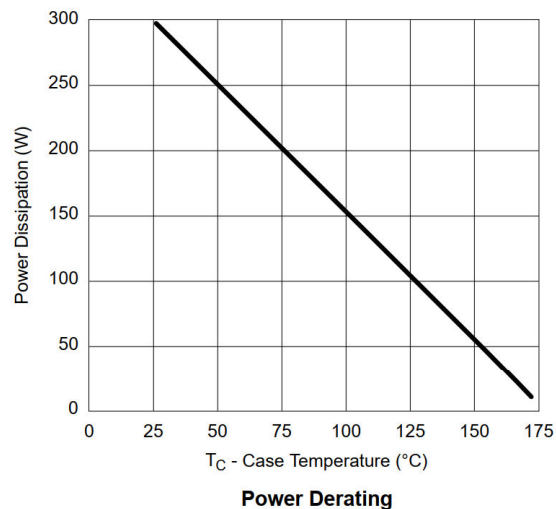
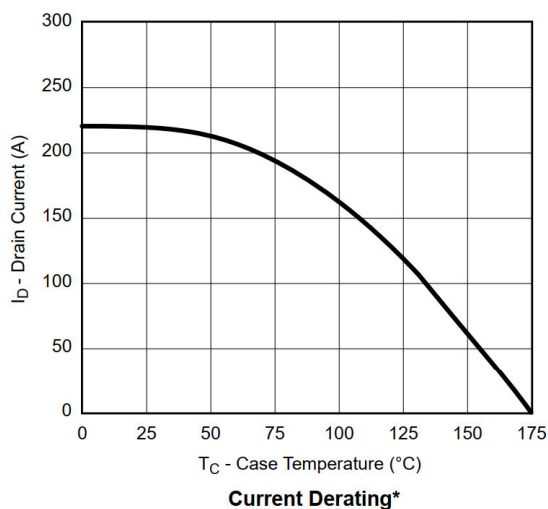


Threshold Voltage

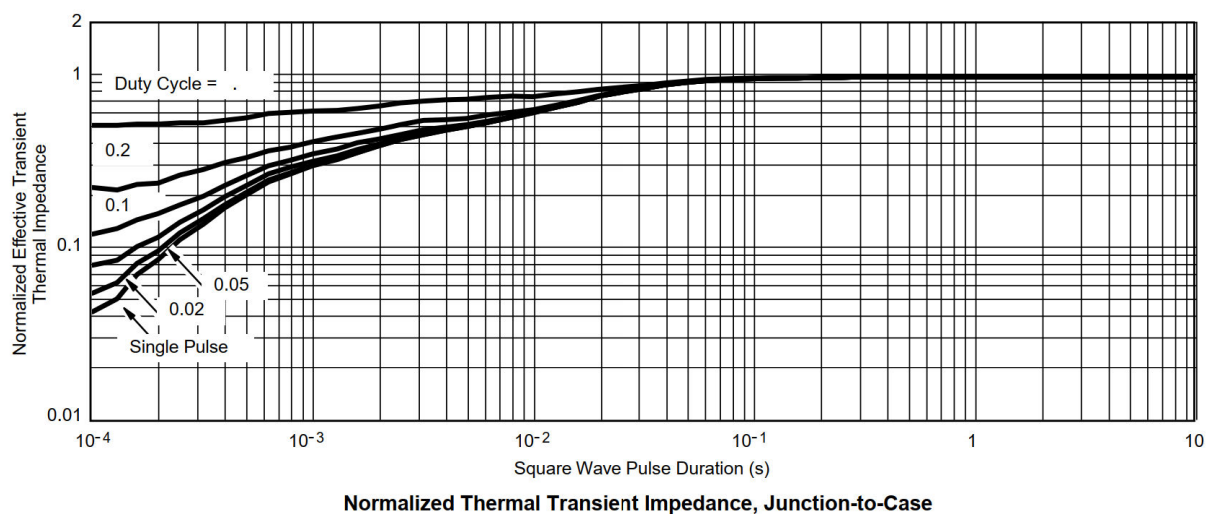


* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient

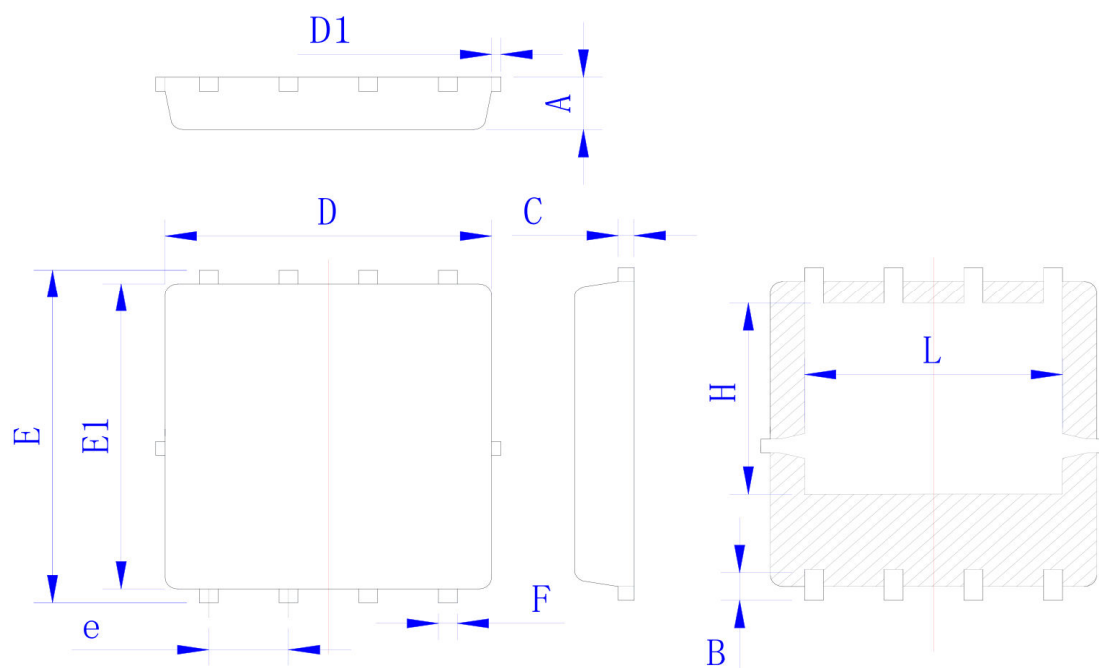
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



DFN5X6_8L PACKAGE OUTLIN



Symbol	Min	Typ	Max
A	0.90	0.95	1.00
B	0.48	0.58	0.68
C	0.20	0.254	0.30
D	5.00	5.20	5.40
D1			0.15
E	5.90	6.05	6.20
E1	5.40	5.55	5.70
e	1.22	1.27	1.32
F	0.25	0.30	0.35
H	3.27	3.47	3.67
L	3.80	4.00	4.20

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